

2N3700  
2N3701

SILICON  
NPN TRANSISTORS



TO-18 CASE



www.centrasemi.com

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR 2N3700 and 2N3701 are silicon NPN transistors designed for high current general purpose applications.

**MARKING: FULL PART NUMBER**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

	SYMBOL		UNITS
Collector-Base Voltage	$V_{CBO}$	140	V
Collector-Emitter Voltage	$V_{CEO}$	80	V
Emitter-Base Voltage	$V_{EBO}$	7.0	V
Continuous Collector Current	$I_C$	1.0	A
Power Dissipation ( $T_C=25^\circ\text{C}$ )	$P_D$	1.8	W
Power Dissipation	$P_D$	500	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +200	$^\circ\text{C}$
Thermal Resistance	$\theta_{JA}$	350	$^\circ\text{C/W}$
Thermal Resistance	$\theta_{JC}$	97.2	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N3700		2N3701		UNITS
		MIN	MAX	MIN	MAX	
$I_{CBO}$	$V_{CB}=90\text{V}$	-	10	-	10	nA
$I_{CBO}$	$V_{CB}=90\text{V}, T_A=150^\circ\text{C}$	-	10	-	10	$\mu\text{A}$
$I_{EBO}$	$V_{EB}=5.0\text{V}$	-	10	-	10	nA
$BV_{CBO}$	$I_C=100\mu\text{A}$	140	-	140	-	V
$BV_{CEO}$	$I_C=30\text{mA}$	80	-	80	-	V
$BV_{EBO}$	$I_E=100\mu\text{A}$	7.0	-	7.0	-	V
$V_{CE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	0.2	-	0.2	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$	-	0.5	-	0.5	V
$V_{BE(SAT)}$	$I_C=150\text{mA}, I_B=15\text{mA}$	-	1.1	-	1.1	V
$h_{FE}$	$V_{CE}=10\text{V}, I_C=0.1\text{mA}$	50	-	30	100	
$h_{FE}$	$V_{CE}=10\text{V}, I_C=10\text{mA}$	90	-	40	120	
$h_{FE}$	$V_{CE}=10\text{V}, I_C=150\text{mA}$	100	300	40	120	
$h_{FE}$	$V_{CE}=10\text{V}, I_C=150\text{mA}, T_A=-55^\circ\text{C}$	40	-	-	-	
$h_{FE}$	$V_{CE}=10\text{V}, I_C=500\text{mA}$	50	-	30	100	
$h_{FE}$	$V_{CE}=10\text{V}, I_C=1.0\text{A}$	15	-	15	-	

R1 (4-March 2014)

2N3700  
2N3701

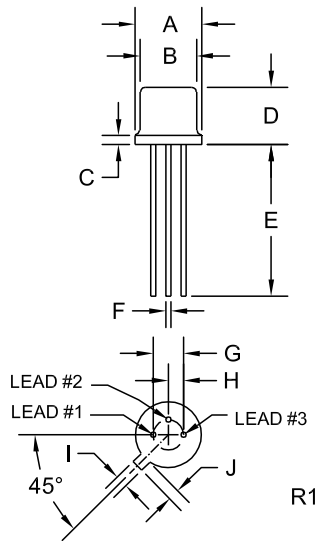
SILICON  
NPN TRANSISTORS



**ELECTRICAL CHARACTERISTICS - Continued:** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N3700		2N3701		UNITS
		MIN	MAX	MIN	MAX	
$f_T$	$V_{CE}=10\text{V}$ , $I_C=50\text{mA}$ , $f=20\text{MHz}$	100	400	80	400	MHz
$C_{ob}$	$V_{CB}=10\text{V}$ , $I_E=0$ , $f=1.0\text{MHz}$	-	12	-	12	pF
$C_{ib}$	$V_{EB}=0.5\text{V}$ , $I_C=0$ , $f=1.0\text{MHz}$	-	60	-	60	pF
$h_{fe}$	$V_{CE}=5.0\text{V}$ , $I_C=1.0\text{mA}$ , $f=1.0\text{kHz}$	80	400	30	200	
$r_b'C_c$	$V_{CB}=10\text{V}$ , $I_E=10\text{mA}$ , $f=4.0\text{MHz}$	25	400	25	400	pS
NF	$V_{CE}=10\text{V}$ , $I_C=100\mu\text{A}$ , $f=1.0\text{kHz}$ , $R_S=1.0\text{k}\Omega$	-	4.0	-	4.0	dB

**TO-18 CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A (DIA)	0.209	0.230	5.31	5.84
B (DIA)	0.178	0.195	4.52	4.95
C	-	0.030	-	0.76
D	0.170	0.210	4.32	5.33
E	0.500	-	12.70	-
F (DIA)	0.016	0.019	0.41	0.48
G (DIA)	0.100		2.54	
H	0.050		1.27	
I	0.036	0.046	0.91	1.17
J	0.028	0.048	0.71	1.22

TO-18 (REV: R1)

**LEAD CODE:**

- 1) Emitter
- 2) Base
- 3) Collector

**MARKING:**

FULL PART NUMBER

R1 (4-March 2014)